LP6451X
18V/3A Synchronous BUCK Switching Converter

Features

- Wide input voltage range: 4.2V – 18V
- Output voltage range: V_{ref} – 7V
- High efficiency operation
  - Integrated a 45-mΩ LS-MOSFET and a 65-mΩ HS-MOSFET
  - 91% efficiency at 3A load from 12V to 5V conversion
- Automatic PFM mode at light load (LP6451X)
- ±2% V_{ref} accuracy at room temperature
- Typical 1.2-MHz switching frequency
- COT control scheme with fast load transient response
- Hiccup protection
- Integrated UVLO, OVP, OCP, SCP, and OTP protections
- 1.25ms typical soft-start time
- 1.6mm X 2.9mm SOT23-6 package
- RoHS Compliant and 100% Lead (Pb) Free

Applications

- Industrial PC
- Network/digital video recorder (NVR/DVR)
- TV and TV box
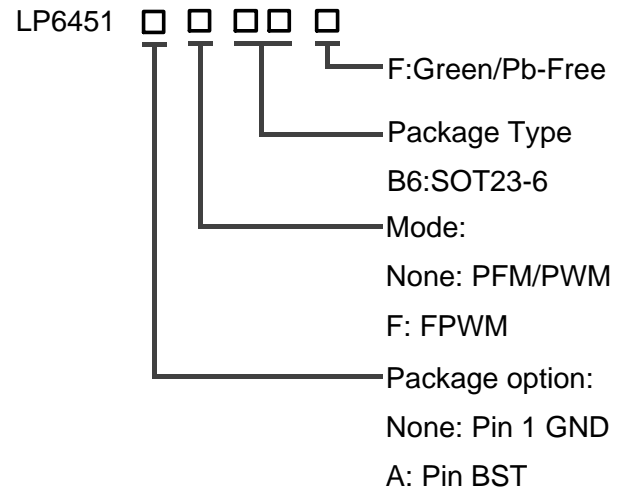- 12V Industrial bus applications

General Description

The LP6451X is a synchronous buck converter supporting up to 3A output current. The LP6451X employs an adaptive constant-on-time (COT) control scheme to achieve fast load transient response. The external components are minimized, requiring only one inductor, two resistors, and two capacitors.

The LP6451X supports both aluminum polymer capacitors and ceramic capacitors without extra compensation components.
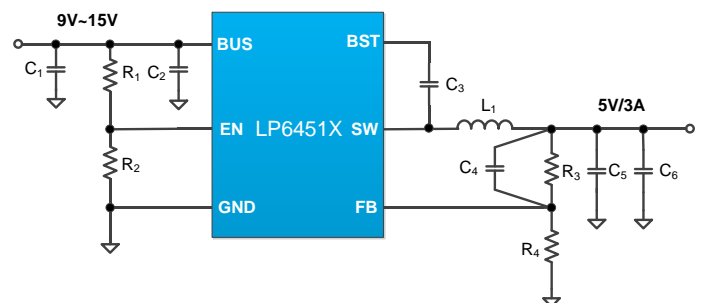
The LP6451X integrates PFM (Pulse Frequency Modulation) operation, which helps maintain the system efficiency at light load while the LP6451XF works in FPWM mode to achieve low output covering all load range. The LP6451X also integrates multiple protection functions, i.e., over-current protection (OCP), over-temperature protection (OTP), under-voltage lockout (UVLO), and short circuit protection (SCP).

The LP6451X is available in a small 6-pin 1.6mmX2.9mm SOT23-6 package.

Order Information

LP6451 ☐ ☐ ☐ ☐ ☐

- F:Green/Pb-Free
- Package Type
  B6:SOT23-6
- Mode:
  None: PFM/PWM
  F: FPWM
- Package option:
  None: Pin 1 GND
  A: Pin BST

Typical Application Circuit

Device Information

| Part Number	Top Marking	Vref	Package	Shipping	MSL
LP6451TB6F	LPS AUYWX	0.76V	SOT23-6	3K/REEL	LEVEL-3
LP6451FB6F	LPS AtYWX	0.76V	SOT23-6	3K/REEL	LEVEL-3
LP6451AB6F	LPS AsYWX	0.592V	SOT23-6	3K/REEL	LEVEL-3
LP6451AFB6F	LPS AuYWX	0.592V	SOT23-6	3K/REEL	LEVEL-3
LP6451MB6F	LPS AvYWX	0.8V	SOT23-6	3K/REEL	LEVEL-3
Marking indication: Y: Year code. W: Week code. X: Batch numbers. **MSL: Moisture Sensitivity Level according to JEDEC Standard.**					

Pin Diagram
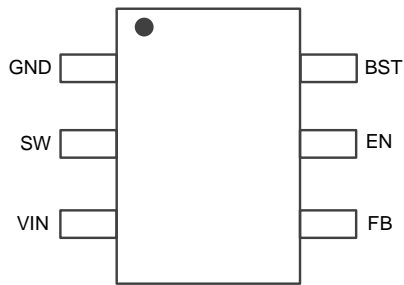
SOT23-6
(Top View)

LP6451T/LP6451M Pinout
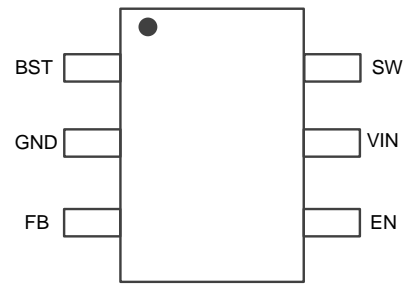
SOT23-6
(Top View)

LP6451A Pinout

Pin Description

Pin # LP6451A	Pin # LP6451T LP6451M	Name	Description
2	1	GND	Power ground of the IC
6	2	SW	The switching node of the converter.
5	3	VIN	IC power supply input.
3	4	FB	Feedback pin. Use a resistor divider to set the desired output voltage
4	5	EN	Enable input. This pin can be used to control the system power sequence as well
1	6	BST	Bootstrap pin. Power supply for high-side MOSFET gate driver. A 0.1-µF capacitor must be connected between this pin and SW pin.

Absolute Maximum Ratings (Note)

VIN, SW, and EN to GND --- -0.3V to 19V

FB to GND -- -0.3V to 6.5V

BST to SW -- -0.3V to 6.5V

SW to GND （5ns transient） --- -3.5V to 20V

Junction Temperature Range (TJ) --- -40℃ to 150℃

Maximum Soldering Temperature (at leads, 10 sec) --260℃

Note: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD Ratings

HBM (Human Body Model) --- 2kV

CDM (Charged-device Model) -- 500V

Thermal Information

θ_{JA} (Junction-to-Ambient Thermal Resistance) --- 140℃/W

Recommended Operating Conditions

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
V_{IN}	Input voltage	4.2		18	V
V_{OUT}	Output voltage	V_{ref}		9	V
L	Inductor	0.7		6.0	μH
T_A	Ambient temperature range	-40		85	°C
C_{IN}	Input decoupling capacitor	4.7		100	μF
C_{OUT}	Output capacitor	10		100	μF

Electrical Characteristics

(The specifications are measured under conditions V_{IN} = 12V, T_A = 25°C, unless otherwise specified.)

SYMBOL	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
INPUT SECTION						
V_{ULVO_R}	Input under voltage lockout threshold	V_{IN} rising threshold		4.0	4.2	V
V_{ULVO_H}	UVLO hysteresis	V_{IN} falling threshold		0.3		V
I_{q_VIN}	Input quiescent current	No switching, EN=3V, FB=1.0V		320		μA
BUCK CONVERTER						
I_{LIM}	Low-side valley current limit	T_A=25°C	2.8	3.8	5.0	A
V_{ref}	Reference voltage	T_A=25°C, LP6451T		0.76		V

SYMBOL	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
		$T_A=25^oC$, LP6451A	0.58	0.592	0.604	V
		$T_A=25^oC$, LP6451M		0.8		V
R_{dson_HS}	High-side FET on resistance	$V_{IN}=12V$		65		mΩ
R_{dson_LS}	Low-side FET on resistance	$V_{IN}=12V$		45		mΩ
F_{sw}	Switching frequency			1200		kHz
t_{on-min}	Minimum on-time[1]			50		ns
$t_{off-min}$	Minimum off-time[1]	$V_{FB}=V_{ref}$ - 0.2V		100		ns
$t_{on-hiccup}$	Hiccup on time[1]			2		ms
$t_{off-hiccup}$	Hiccup waiting time[1]			32		ms
t_d	EN delay time[1]	From EN high to first switching		250		us
t_{ss}	Soft-start time[1]	From first switching to 95%Vref		1		ms
T_{jsd}	Thermal shutdown threshold	Rising threshold		160		^oC
	Thermal shutdown threshold	Falling threshold		135		^oC
I_{leak_FB}	FB pin leakage current			0.01		µA
EN Logic						
V_H	EN pin logic high threshold	EN Rising threshold		1.2		V
V_{hys}	EN pin threshold hysteresis			0.2		V
	EN pin internal pull-down resistance			1000		kΩ

[1]: Not production tested. Guaranteed by design

Typical Characteristics (VIN=12V)
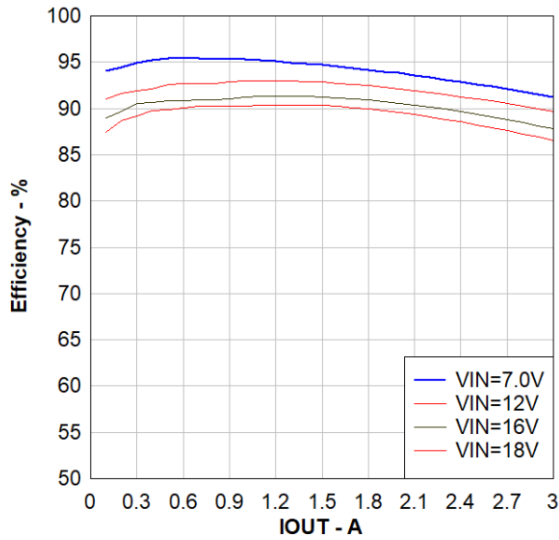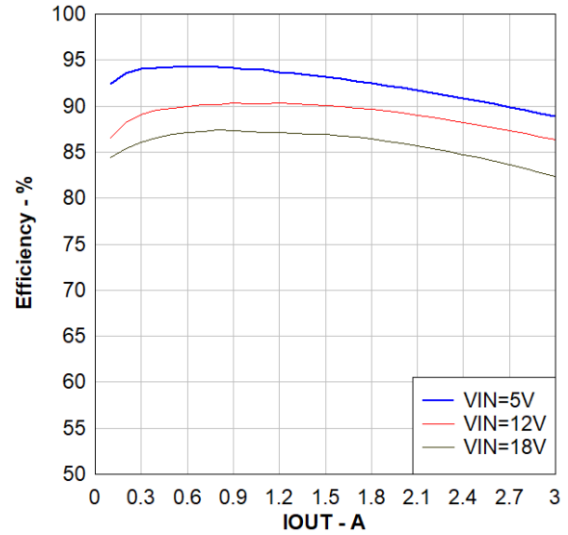

Figure 1. VOUT=5V, Efficiency, L=2.2uH

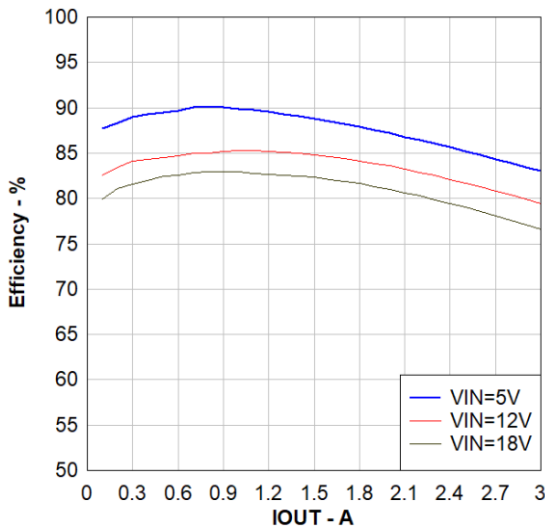Figure 2. VOUT=3.3, Efficiency, L=2.2uH

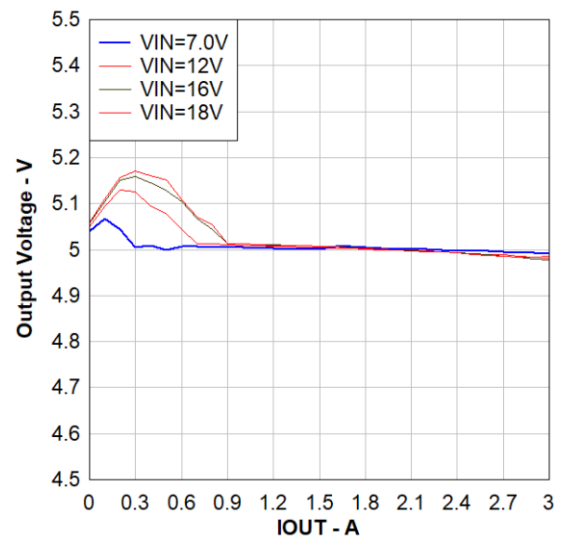Figure 3. VOUT=1.8V, Efficiency, L=1uH
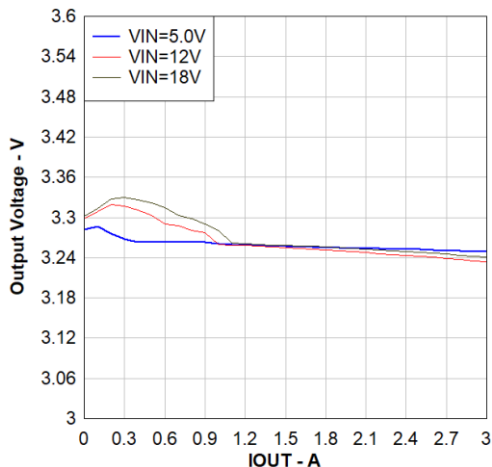

Figure 3. VOUT=5V, Regulation, L=2.2uH

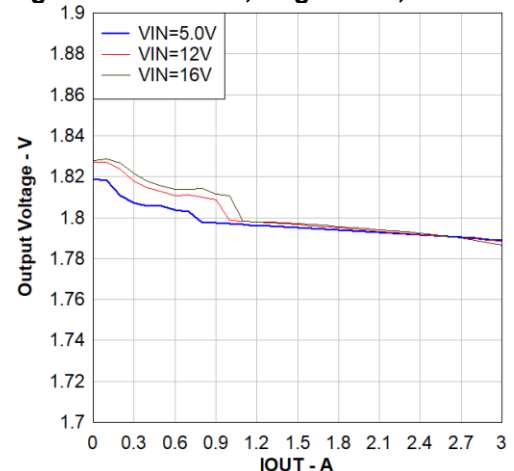Figure 4. VOUT=3.3V, Regulation, L=2.2uH

Figure 5. VOUT=1.8V, Regulation, L=1uH

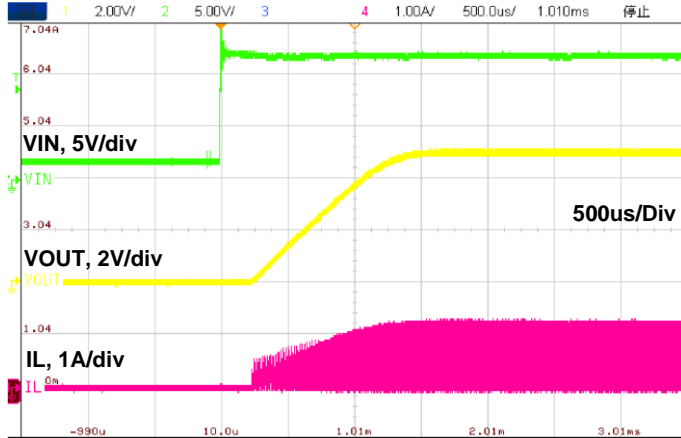## Application Waveforms (Vin=12V, L=2.2uH, Cout=22uF*2)
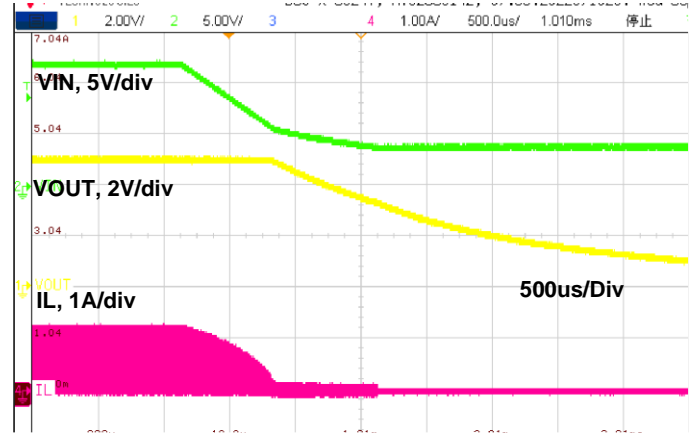

Figure 6. Startup by VIN, 50Ω load
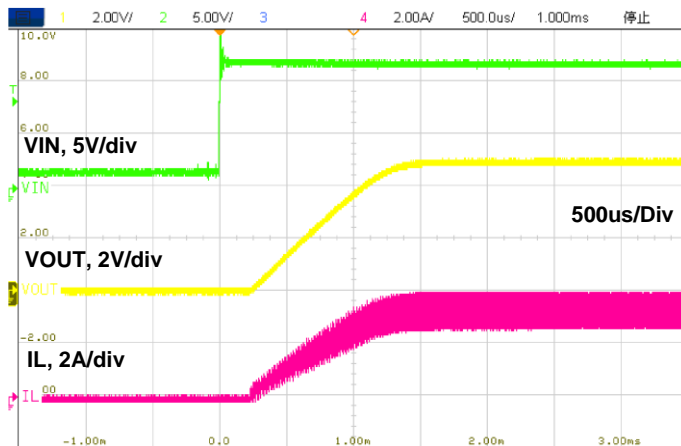

Figure 7. Shutdown by VIN, 50Ω load

Figure 8. Startup by VIN, 1.7Ω load
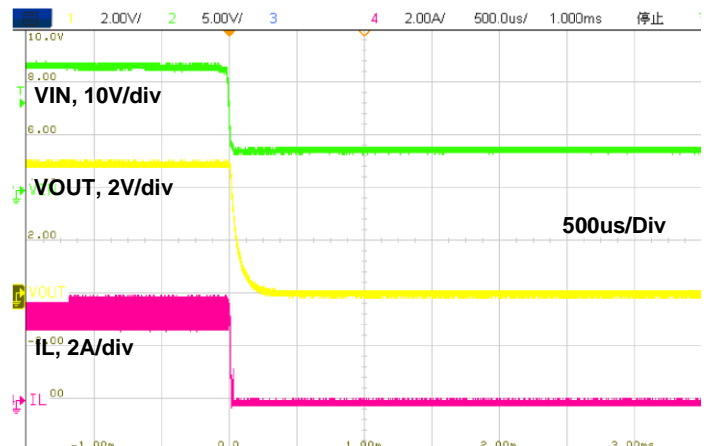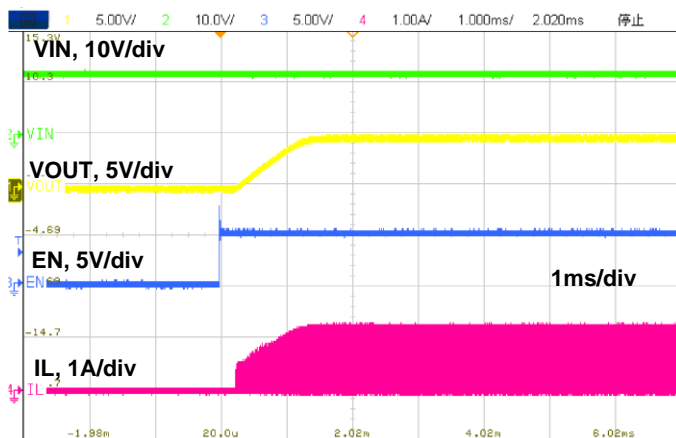

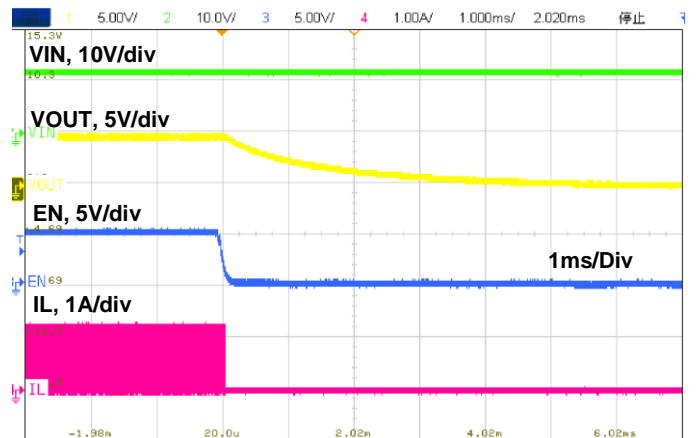Figure 9. Shutdown by VIN, 1.7Ω load

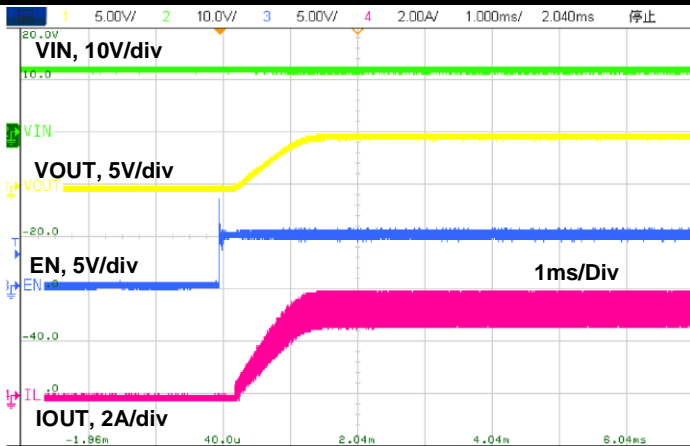Figure 10. Startup by EN, 50Ω load

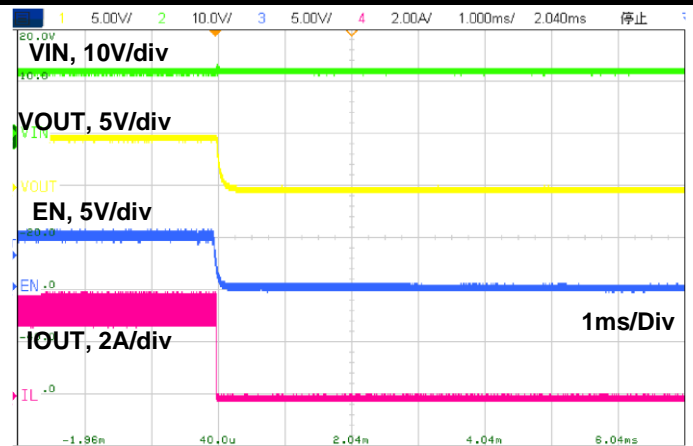Figure 11. Shutdown by EN, 50Ω load

Figure 12. Startup by EN, 1.7Ω load
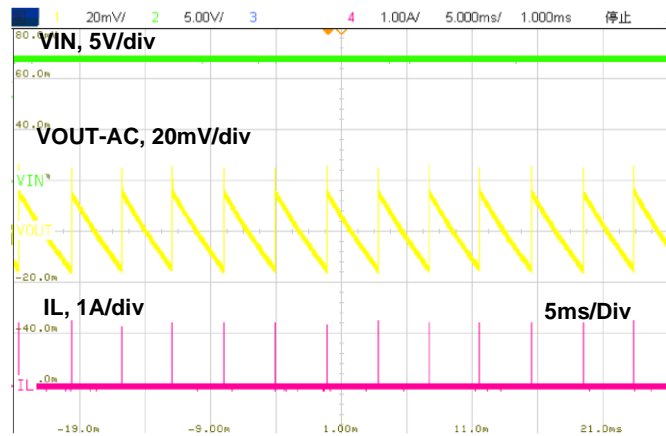

Figure 13. Shutdown by EN, 1.7Ω load

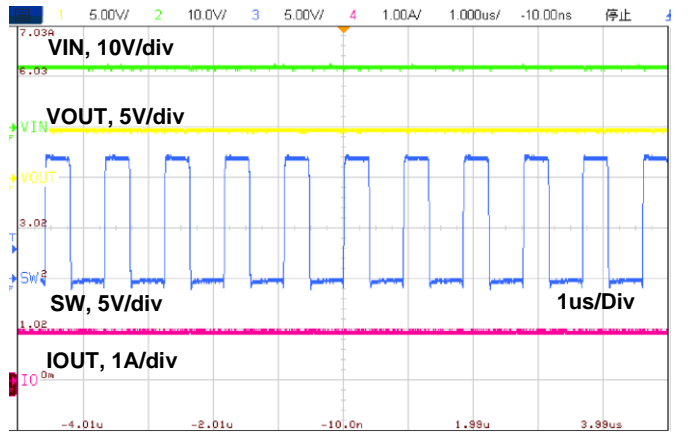**Figure 14. Switching Waveform, 0A load**
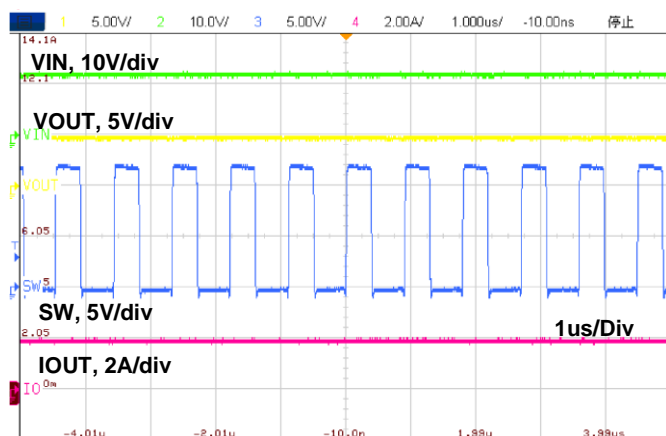

Figure 15. Switching Waveform, 1A load

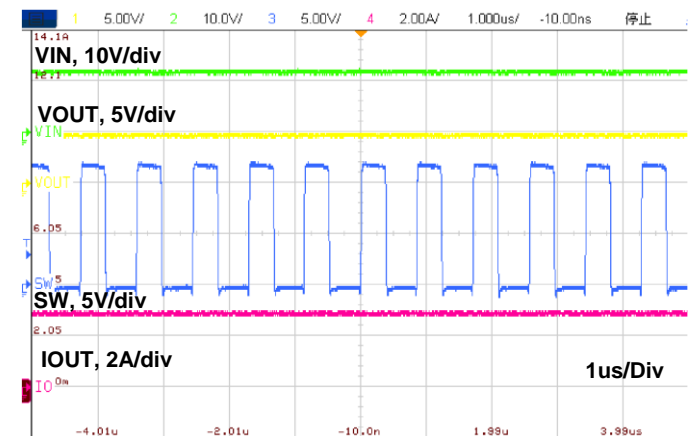**Figure 16. Switching Waveform, 2A load**
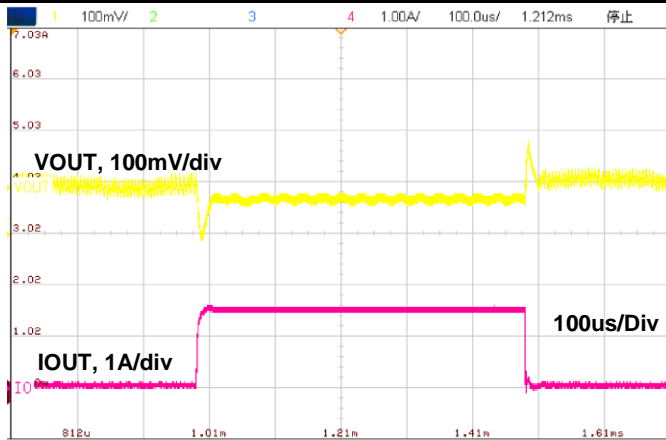

Figure 17. Switching Waveform, 3A load

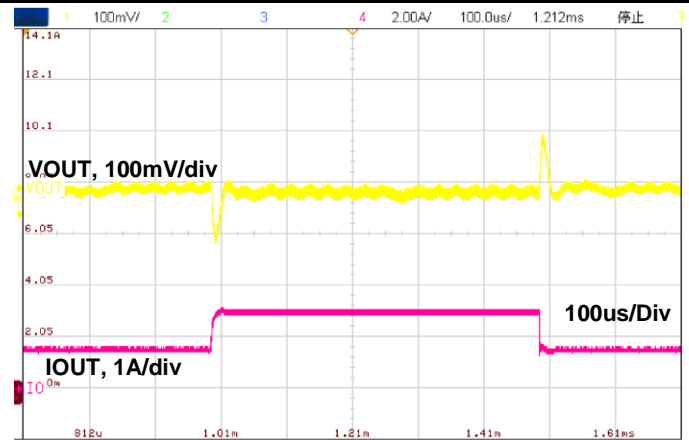Figure 18. Load Transient, 0.1A-1.5A-0.1A
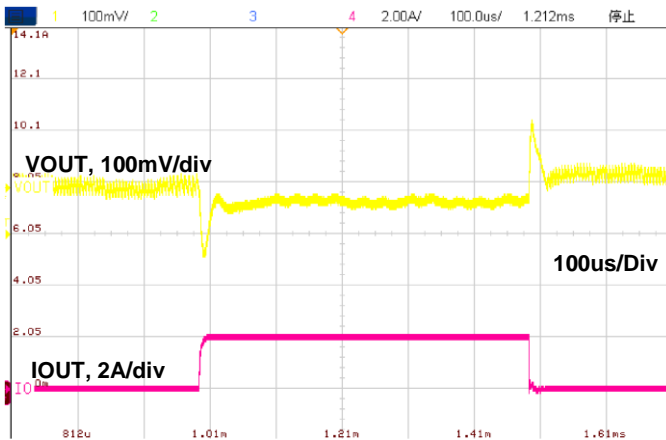

Figure 19. Load Transient, 1.5A-3A-1.5A

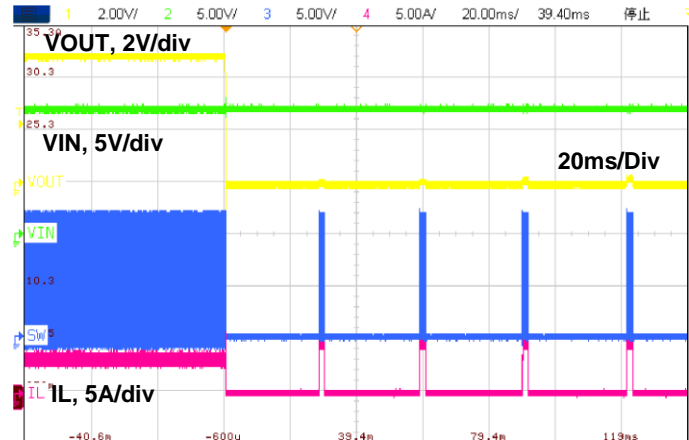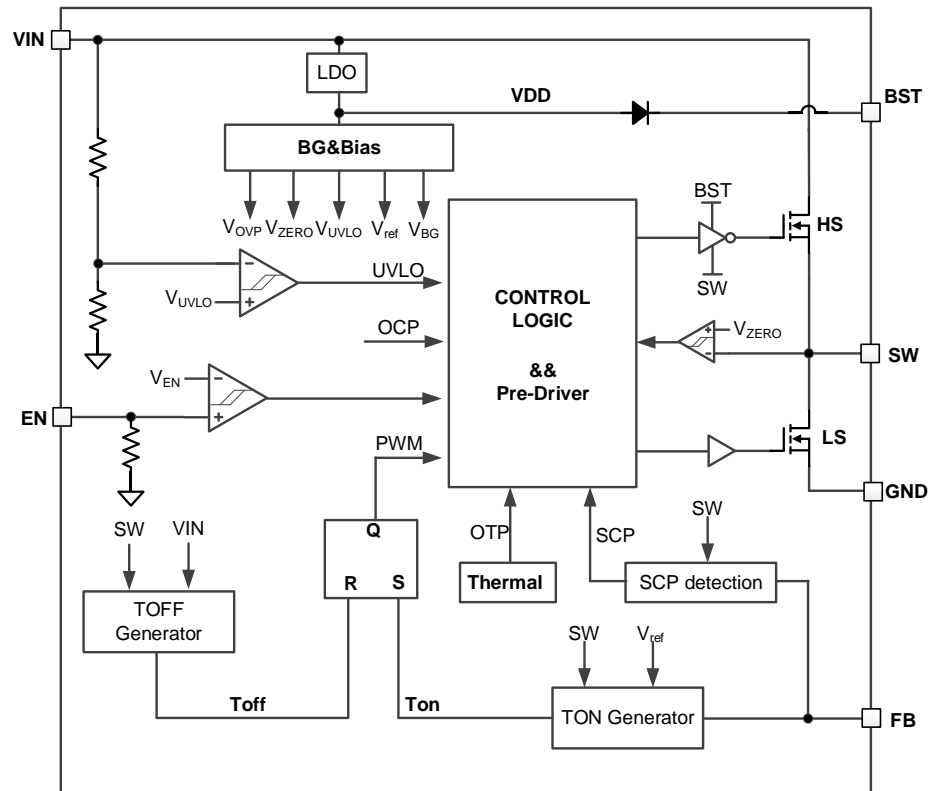Figure 20. Load Transient, 0.1A-2A-0.1A

Figure 21. Current Limit Operation

Functional Block Diagram

Detailed Description

Overview

The LP6451X is a 3A synchronous buck converter, supporting 4.2-18V input voltage range. The adaptive COT control scheme enables fast transient respond and minimizes the output capacitance. The LP6451X supports both aluminum polymer capacitors and low-ESR ceramic capacitors without external compensation circuit. The LP6451X automatically transfers between PFM and PWM according to the output current.

Under Voltage Lockout (UVLO)

When the input voltage VIN is lower than the UVLO threshold, all functions are shut down. When the input voltage is higher than the UVLO rising threshold, the LP6451X can be enabled by the EN pin.

EN Control

The EN pin can be used to control the system power-up sequence. A precise voltage reference is used as the threshold. When the VIN is above the UVLO threshold and EN voltage rises above the EN pin logic high threshold (1.2V typically), the LP6451X enables all the internal circuits, delays for 260us, and begins the soft-start (refer to Soft-start section for more details).

The EN pin has an internal 1000kΩ pull-down resistor to ground.

Soft-start

The LP6451X integrates soft-start function with a typical time of 1.25ms (t_{ss}) . After passing the UVLO threshold and enabled by the EN pin with the 250us delay(t_d), the internal reference voltage ramps from zero to the Vref in 1.25-ms and the output voltage ramps up accordingly.
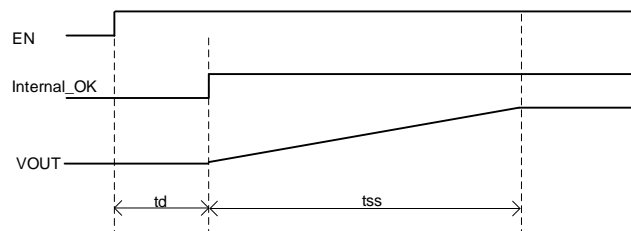

Figure 22. Soft Start Sequence

Constant-ON Time (COT) Control Scheme

The LP6451X integrates the COT control scheme for pseudo-fixed- frequency operation when operating in continuous conduction mode (CCM). Refer to the Functional Block Diagram for better understanding of the operation. The internal on-time (TON) generator block monitors the FB-pin voltage and turns on the high-side MOSFET to start a switching cycle, when the FB-pin voltage drops to an internal reference voltage Vref. Then the internal circuits start to calculate the on-time of the high-side MOSFET, which is proportional to the input voltage and inversely proportional to the output voltage. Once the on-time is finished, the TOFF generator turns off the high-side MOSFET and turns on the low-side MOSFET.

PFM Operation

The LP6451X is designed to maintain high efficiency at light load by adopting pulse-frequency modulation (PFM). In the PFM, the switching cycle is still initiated by the TON generator monitoring the FB-pin voltage. The high-side MOSFET is turned on for TON time and then turned off, followed by turning on the low-side MOSFET. The inductor current falls when the low-side MOSFET is on. When the inductor current reaches zero, detected by the zero-current detection (ZCD) comparator, the low-side MOSFET is turned off, together with the high-side MOSFET. Both MOSFETs remains off until a new switching cycle begins, determined by TON generator. As the load current decreases, the duration for both MOSFETs to remain off increases, leading to a lower switching frequency and higher power efficiency.

FPWM Operation (LP6451F/LP6451AF)

The LP6451F is designed to work at FPWM to maintain the good regulation and transient performance. When the output decreases, the inductor is allowed to flow from the output to the ground plane. In this way, the switching frequency is kept the same even without load.

The FPWM operation mode reduced the output ripple under light load at the cost of lower light load efficiency

Bootstrap Capacitor

The LP6451X integrates two N-MOSFET to achieve high efficiency. The high-side MOSFET is powered by the bootstrap capacitor CBST, which is between the BST pin and SW pin.

Over Current Protection and Short Circuit Protection

The LP6451X protects an over current situation by limiting the inductor valley current. The current of low-side MOSFET is monitored all the time to sense the inductor valley current when the LP6451X is enabled. The high-side MOSFET cannot be turned on if the valley current is higher than the low-side valley current limit, protecting the inductor current from further increasing. The inductor current is limited to the valley current limit pluses a half of the inductor ripple current.

The SCP is realized by monitoring the FB-pin voltage when the inductor current is limited. Once the output load draws more current than the current limit, the output voltage drops. When the FB voltage drops to 50% of the Vref for 1.5-ms, the LP6451X shuts down. The LP6451X will restart after a typical 32-ms hiccup waiting time. If the SCP condition still holds after soft-start, the LP6451X shutdown again, repeating the hiccup operation.

When the over current condition is removed, the output voltage returns to normal operation.

Thermal Protection

The LP6451X has a thermal protection function. The device will shut down when the internal temperature is higher than 160°C and will restart after the temperature drops below 135°C.

Application Information

Design Requirements

The table 1 shows the design parameters for a typical 5V output voltage in the IPC application.

Table 1 Design Parameters

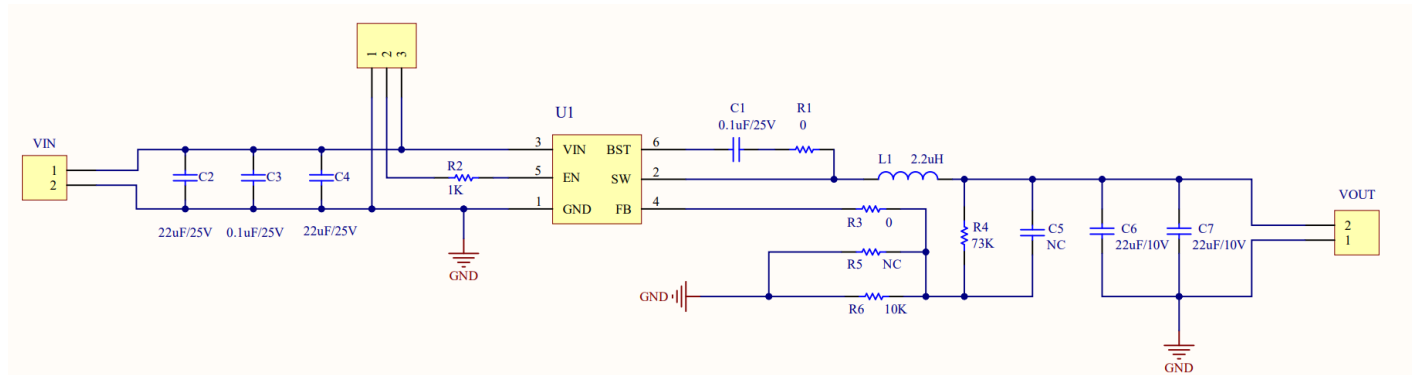| Parameter	Target
Input voltage range	9~15V
Output voltage	5V
Transient ripple	±200mV
Operating frequency	1200kHz

Figure 23. Typical schematic

Output Voltage Setting

The output voltage can be programmed by adjusting the external resistor divider R_{UP} and R_{DOWN} according to the equation below:

$$V_{OUT} = \left(\frac{R_{UP}}{R_{DOWN}} + 1\right) * V_{ref}$$

When the output voltage is in regulation, the typical voltage at FB pin is 0.6V for LP6451A.

For better accuracy, the R_{DOWN} is recommended to be lower than 100kΩ to ensure the current flowing through R_{DOWN} is at least 100 times larger than the FB pin leakage current.

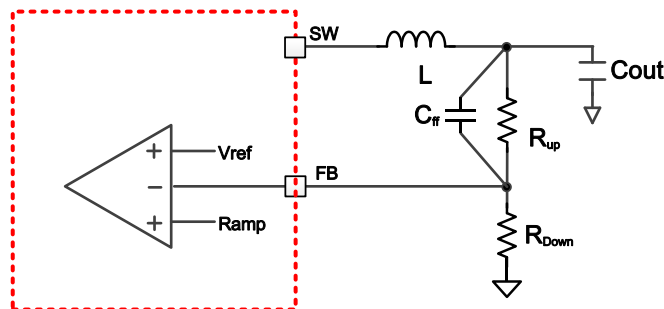For a 5V-output application, a 10kΩ R_{DOWN} is selected and the R_{UP} is 73.2kΩ.

Figure 24. FB connection

EN Design

The LP6453X allows the user to design a precise VIN voltage to enable the converter during power on. The startup sequence can be designed by adjusting the resistor divider of R_{UP_EN} and R_{DOWN_EN} with the equation below,

$$V_{EN} = \frac{1000k\Omega // R_{DOWN\_EN}}{R_{UP\_EN} + 1000k\Omega // R_{DOWN\_EN}} * VIN$$

where V_{EN} is the EN rising threshold voltage at which the converter is enabled, which is 1.2V typically. A 47pF-1nF capacitor is recommend to be soldered in parallel with the R_{EN_DOWN} to avoid the high-frequency noise influence from the switching node.
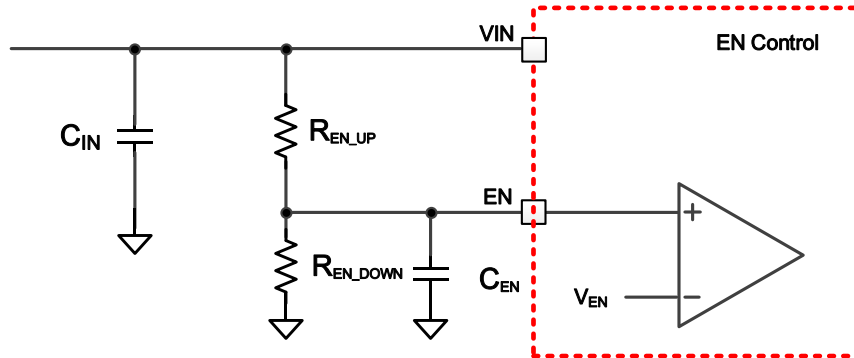

Figure 25. EN connection

Inductor and Output Capacitor Setting

The inductor ripple is calculated by the equation below:

$$I_{PP} = \left(\frac{V_{OUT}}{L * Fsw} * \frac{V_{IN} - V_{OUT}}{V_{IN}} \right)$$

To get a better efficiency, the inductor ripple is recommended to be controlled under 40% of the output current to minimize the AC loss of the inductor and power MOSFETs.

For a typical 12V input voltage and 5V output voltage, a low DCR value, 2.2-µH inductor is recommended.

The output capacitor not only impacts the output ripple but also the loop stability. Please follow the design rules in the table below. A feedforward capacitor C_{FF} can be selected to improve the transient behavior. The typical capacitance can be 10-100pF. For this design, 10V, X5R, 22µF capacitors (GRM21BR61A226ME51) from Murata are soldered at the VOUT to GND. Multiple capacitors should be soldered to keep the system stable because of the voltage rating effect.

Table 2 Recommend R/L/C values (LP6451A)

Vout	Inductor-L	Cout	R_{UP}	R_{DOWN}	C_{ff}
1.2V	1µH/1.2µH	22µF*1	10 kΩ	10 kΩ	NA
3.3V	1.5µH/2.2µH	22µF*2	45 kΩ	10 kΩ	10-100pF
5.0V	2.2µH ~4.7µH	22µF*3(2.2uH) 22µF*2(3.3uH)	73.2 kΩ	10 kΩ	10-100pF

Bootstrap capacitor

A 0.1-µF ceramic capacitor is needed to supply power for the high-side N-MOSFET driver. The capacitor should be at least 10V.

Input capacitor

A typical 22-µF ceramic capacitor is needed to serve as the bulk capacitor at the VIN pin. An additional 0.1µF is strongly recommended to provide additional high frequency filtering and should be placed to the VIN pin and GND as close as possible.

PCB Layout Guidelines

Proper layout of the components to minimize high frequency current path loop is important to prevent electrical and magnetic field radiation and high frequency resonant problems. Follow this specific order carefully to achieve the proper layout.

- Place input capacitor (C_2 and C_4) as close as possible to VIN pin and GND pin and use shortest copper trace connection or GND plane.
- Put output capacitor near to the inductor output terminal and the device. Ground connections need to be tied to the IC ground with a short copper trace or GND plane
- Place inductor input terminal to SW pin as close as possible and limit SW node copper area to lower electrical and magnetic field radiation. Do not use multiple layers in parallel for this connection. Minimize parasitic capacitance from this area to any other trace or plane.
- R_1 is reserved to slow down the switching speed for noise sensitive applications and R_3 with higher than 1kΩ resistor should be soldered if the feedforward capacitor is soldered at the same time.

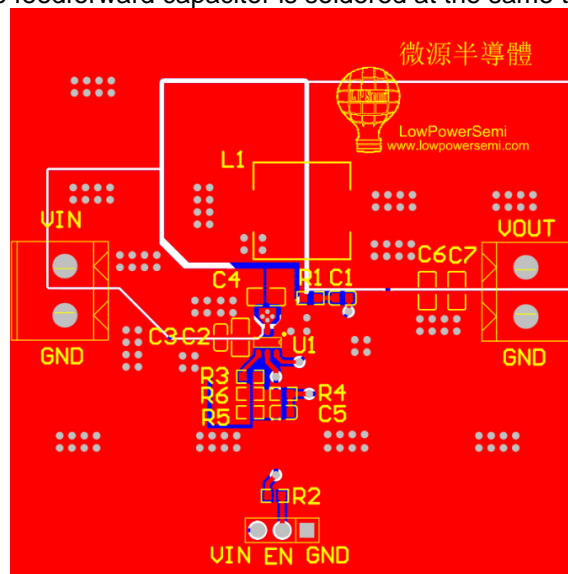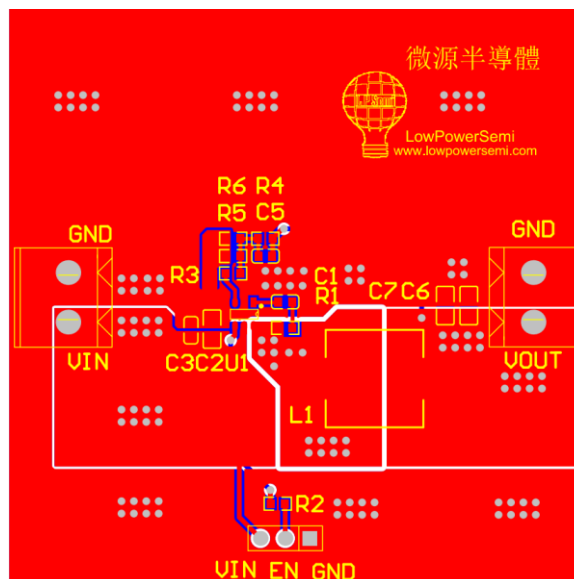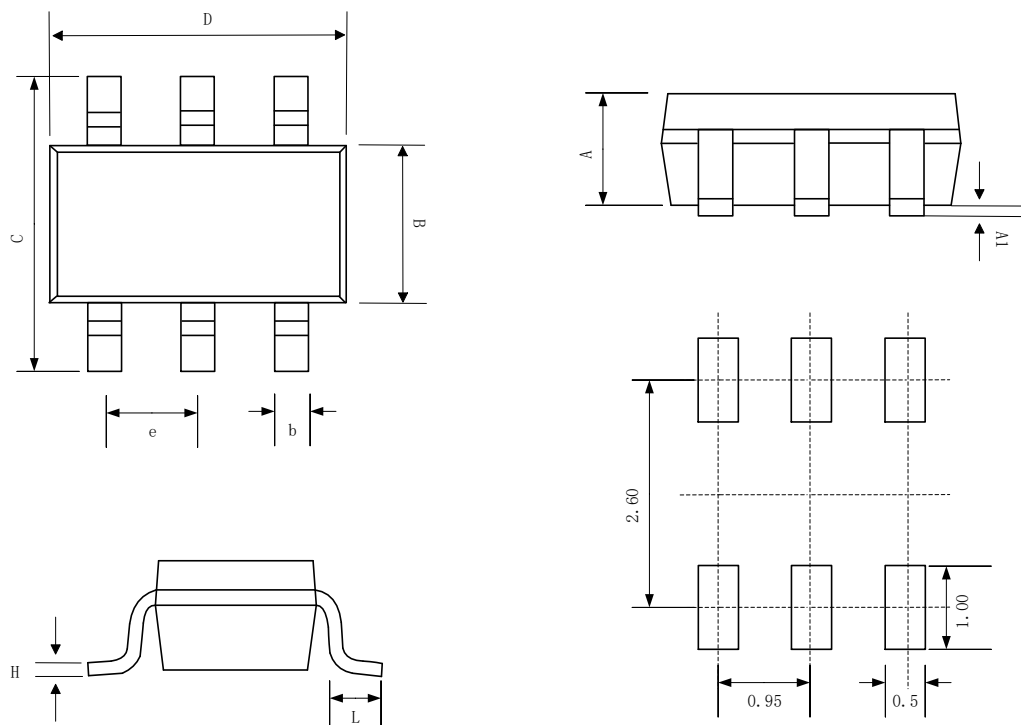**Figure 26 Layout example (LP6451T/LP6451M)**

Figure 27 Layout example (LP6451A)

Packaging Information

1.6x2.9 SOT23-6 package

Recommended Land Pattern

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.889	1.100	1.295
A1	0.000	0.050	0.152
B	1.397	1.600	1.803
b	0.28	0.35	0.559
C	2.591	2.800	3.000
D	2.692	2.920	3.120
e	0.95BSC		
H	0.080	0.152	0.254
L	0.300	0.450	0.610

Revision History

Revision	Date	Change Description
Rev 1p0	11/10/2021	First release version
Rev 1P3	10/27/2023	New format update
Rev 1P4	11/02/2023	Vref accuracy update